

ABSTRACT

5       The present invention provides a high resistivity,  
high quality, large size SiC single crystal, SiC single  
crystal wafer, and method of production of the same, that  
is, a silicon carbide single crystal containing  
uncompensated impurities in an atomic number density of  $1 \times 10^{15}/\text{cm}^3$  or more and containing vanadium in an amount  
less than said uncompensated impurity concentration,  
10       silicon carbide single crystal wafer obtained by  
processing and polishing the silicon carbide single  
crystal and having an electrical resistivity at room  
temperature of  $5 \times 10^3 \Omega\text{cm}$  or more, and a method of  
production of a silicon carbide single crystal.